## Tarni Aggarwal

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Carrier-Induced Defect Saturation in Green InGaN LEDs: A Potential Phenomenon to Enhance Efficiency at Higher Wavelength Regime. ACS Photonics, 2021, 8, 926-932.	6.6	13
2	Role of defect saturation in improving optical response from InGaN nanowires in higher wavelength regime. Nanotechnology, 2020, 31, 495705.	2.6	11
3	Determination of strain relaxation in InGaN/GaN nanowalls from quantum confinement and exciton binding energy dependent photoluminescence peak. Scientific Reports, 2018, 8, 8404.	3.3	10
4	Theoretical modelling of exciton binding energy, steady-state and transient optical response of GaN/InGaN/GaN and AlGaN/GaN/AlGaN core–shell nanostructures. Nanotechnology, 2019, 30, 274002.	2.6	10
5	Engineering V-shaped pits in InGaN layers grown by PA-MBE toward optimizing the active region of green LEDs. Journal of the Optical Society of America B: Optical Physics, 2019, 36, 616.	2.1	10
6	Impact of distributed Bragg reflector on carrier and photon dynamics in GaN-based surface emitting diodes manifested by ultrafast transient absorption spectroscopy. Japanese Journal of Applied Physics, 2019, 58, SCCC15.	1.5	6
7	Enhanced luminescence from InGaN/GaN nano-disk in a wire array caused by surface potential modulation during wet treatment. Nanotechnology, 2019, 30, 104001.	2.6	6
8	Femto-Second Carrier and Photon Dynamics in Site Controlled Hexagonal InGaN/GaN Isolated Quantum Dots: Natural Radial Potential Well and Its Dynamic Modulation. ACS Photonics, 2020, 7, 2555-2561.	6.6	6
9	Carrier Recovery from Sub-Bandgap States in a GaN-Based Quantum-Confined Structure: Identification of Carrier Reservoirs through Femtosecond Pump-Probe Spectroscopy. Journal of Physical Chemistry C, 2021, 125, 3535-3541.	3.1	5
10	Investigation of Ultrafast Carrier Dynamics in InGaN/GaNâ€Based Nanostructures Using Femtosecond Pump–Probe Absorption Spectroscopy. Physica Status Solidi (B): Basic Research, 2021, 258, 2100223.	1.5	3
11	Reduced Auger Coefficient through Efficient Carrier Capture and Improved Radiative Efficiency from the Broadband Optical Cavity: A Mechanism for Potential Droop Mitigation in InGaN/GaN LEDs. ACS Applied Materials & Interfaces, 2022, 14, 13812-13819.	8.0	3
12	Gradual Carrier Filling Effect in "Green―InGaN/GaN Quantum Dots: Femtosecond Carrier Kinetics with Sequential Two-Photon Absorption. ACS Applied Materials & Interfaces, 2021, 13, 45033-45039.	8.0	2
13	Determining the carrier decay kinetics in QCSE-exhibiting materials: An accurate interpretation of transient absorption spectroscopy data. , 2021, , .		1
14	Carrier De-trapping from the Sub-bandgap States: A novel mechanism in InGaN/GaN systems manifested by ultrafast pump-probe spectroscopy. , 2021, , .		0